

FIG.1

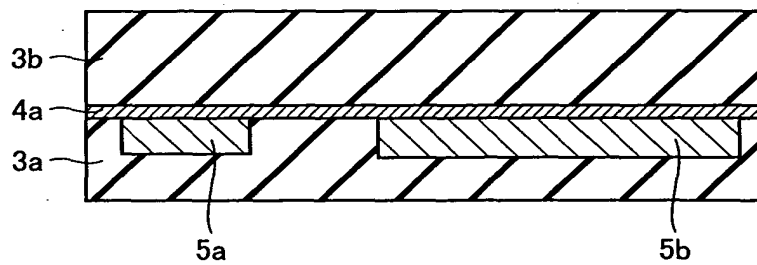


FIG.2

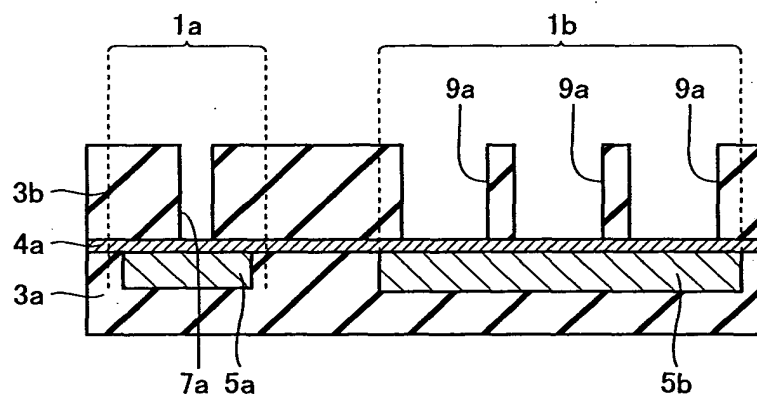


FIG.3A

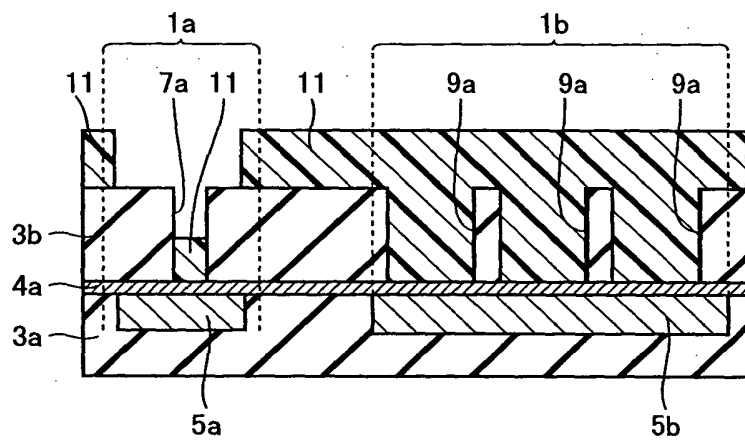


FIG.3B

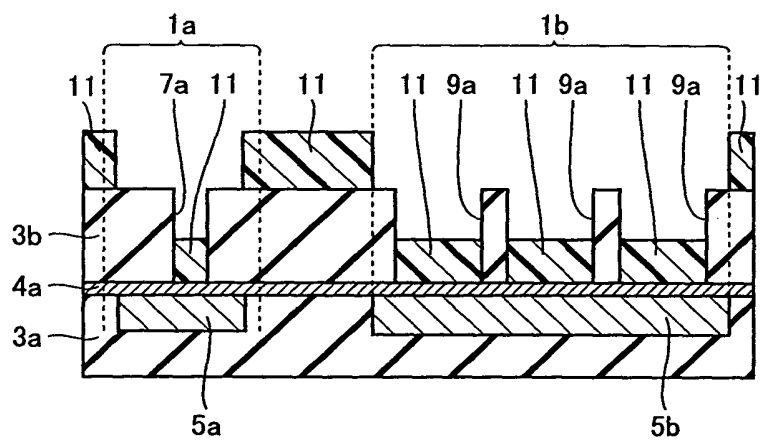


FIG.4A

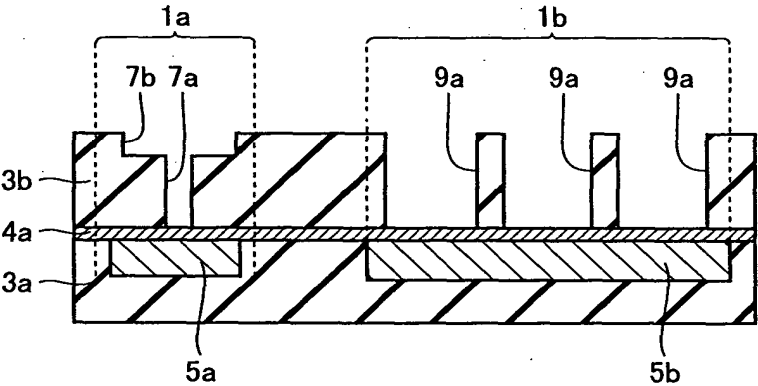


FIG.4B

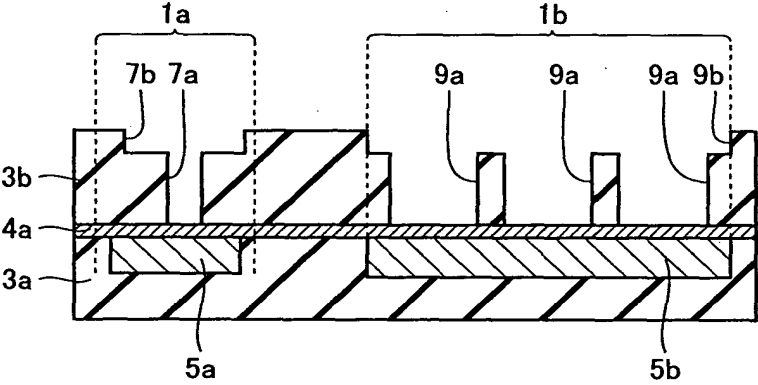


FIG.5

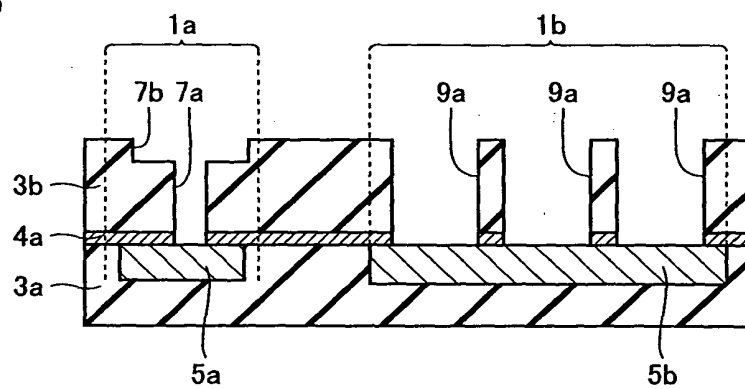


FIG.6

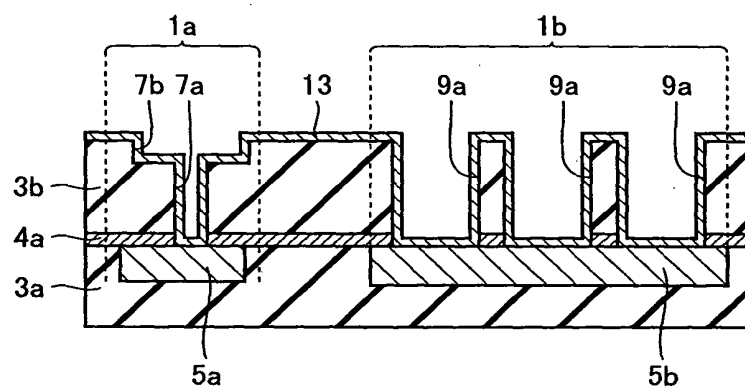


FIG.7

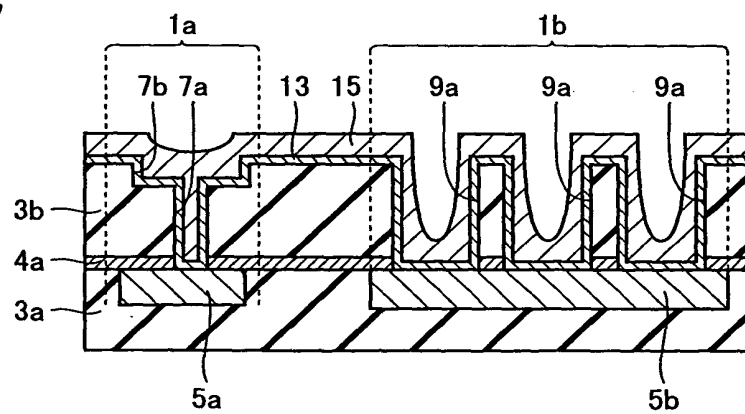


FIG.8

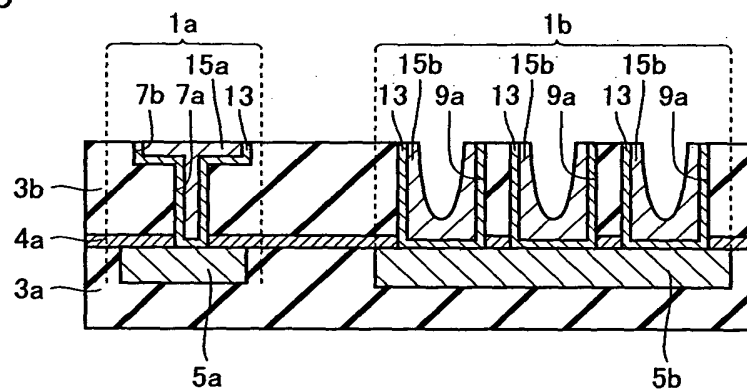


FIG.9

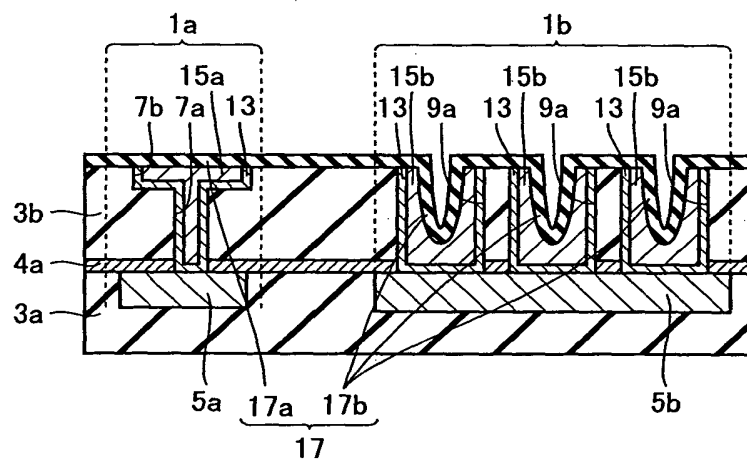


FIG.10

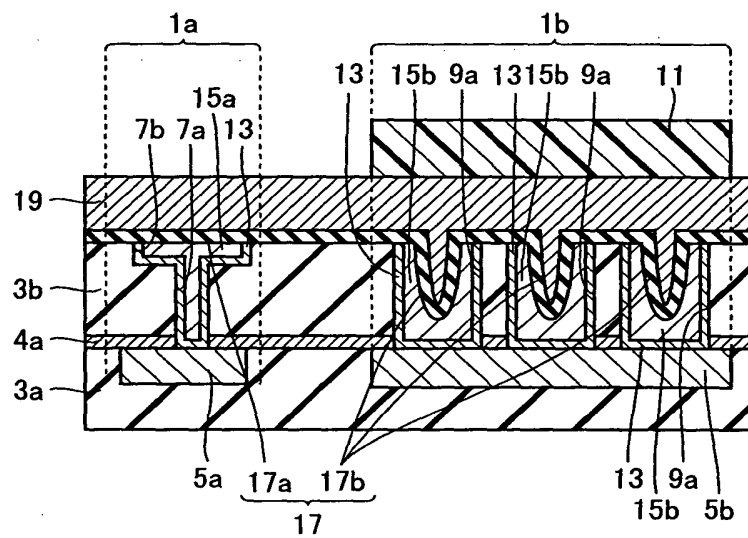


FIG.11A

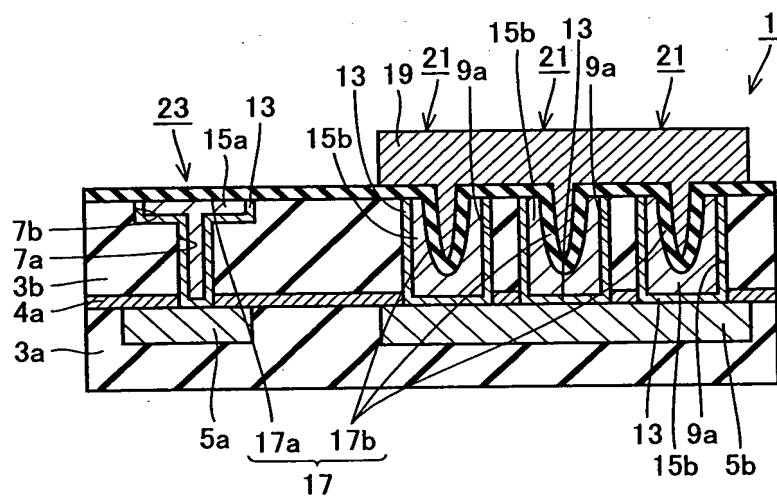
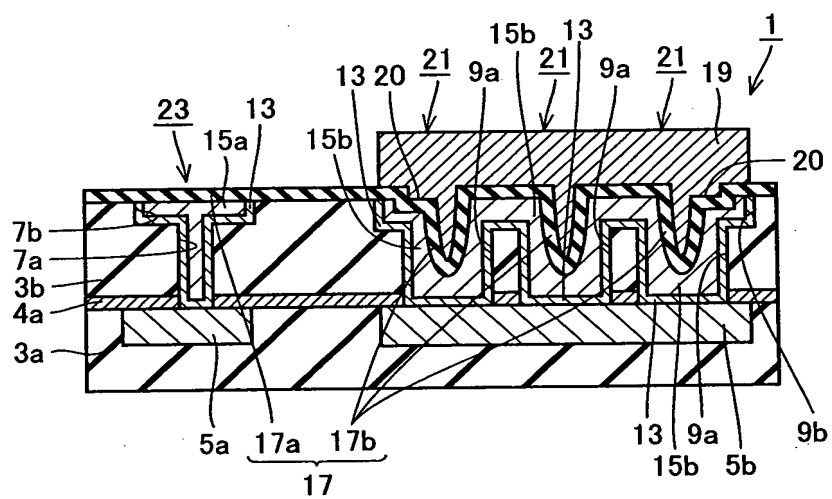


FIG.11B



This cross-sectional diagram illustrates a semiconductor device with two distinct regions, 1a and 1b, separated by a dashed vertical line labeled 17. The top surface is indicated by 3c. In region 1a, there is a vertical stack of layers labeled 7b, 7a, 3b, 4a, and 3a, which sits on a base layer 5a. In region 1b, there are multiple vertical structures, each consisting of a central core 9a surrounded by a layer 15b, all resting on a common base layer 5b.

This cross-sectional view shows a semiconductor device with a multi-layered structure. The top layer is labeled 17, which is divided into regions 17a and 17b. Below this, there are several layers and structures labeled with numbers 1 through 17. The device features a series of vertical structures (17a, 17b) and a series of horizontal structures (17c, 17d). The layers are labeled 1a, 1b, 1c, 1d, 1e, 1f, 1g, 1h, 1i, 1j, 1k, 1l, 1m, 1n, 1o, 1p, 1q, 1r, 1s, 1t, 1u, 1v, 1w, 1x, 1y, 1z. The device is shown in a cross-sectional view, with various layers and structures labeled with numbers 1 through 17. The layers are labeled 1a, 1b, 1c, 1d, 1e, 1f, 1g, 1h, 1i, 1j, 1k, 1l, 1m, 1n, 1o, 1p, 1q, 1r, 1s, 1t, 1u, 1v, 1w, 1x, 1y, 1z. The device is shown in a cross-sectional view, with various layers and structures labeled with numbers 1 through 17.



FIG.14

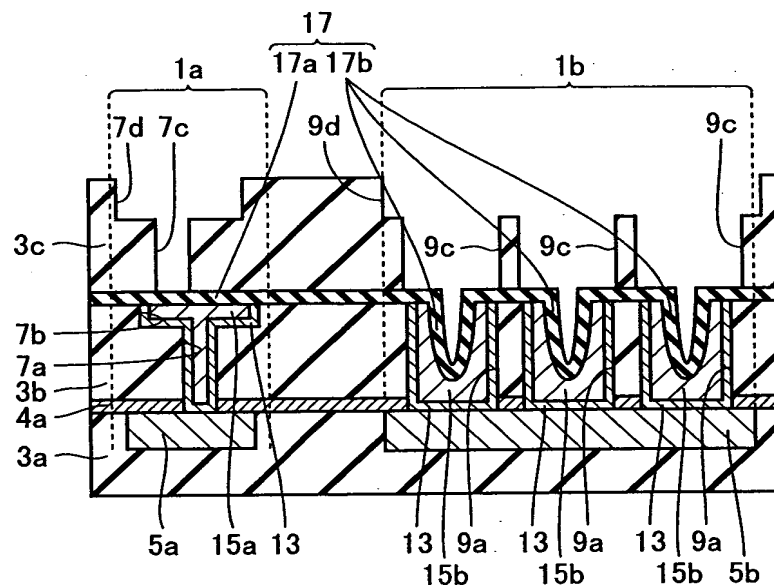


FIG.15

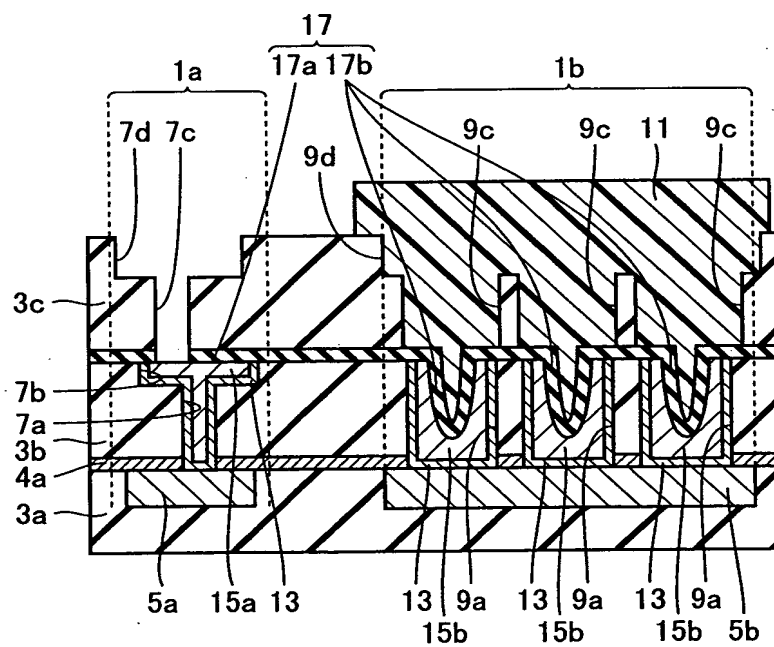


FIG.16

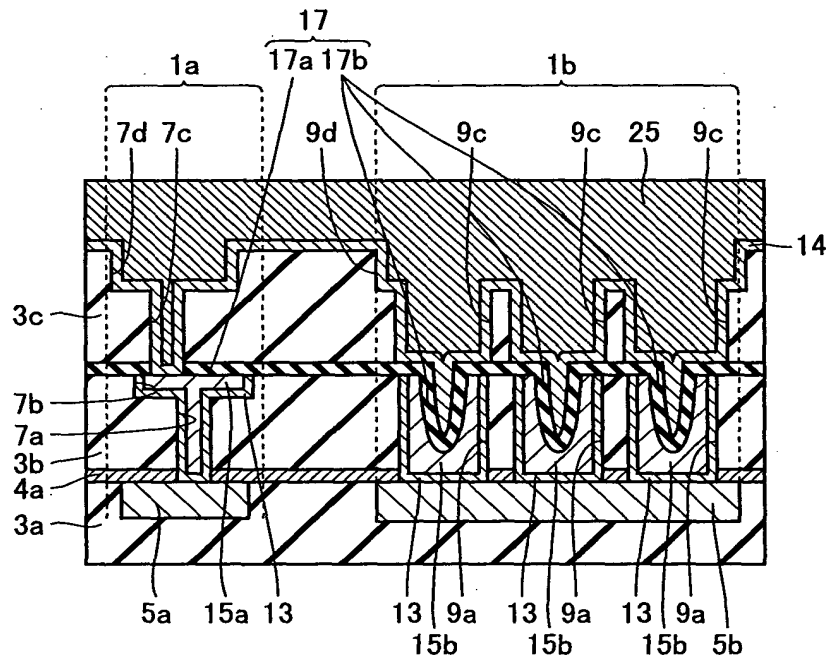


FIG.17

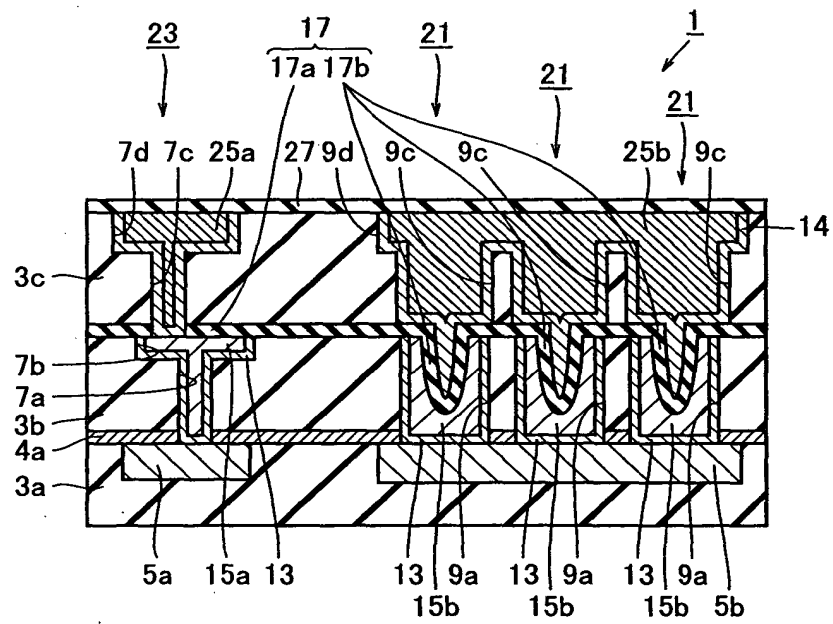


FIG.18

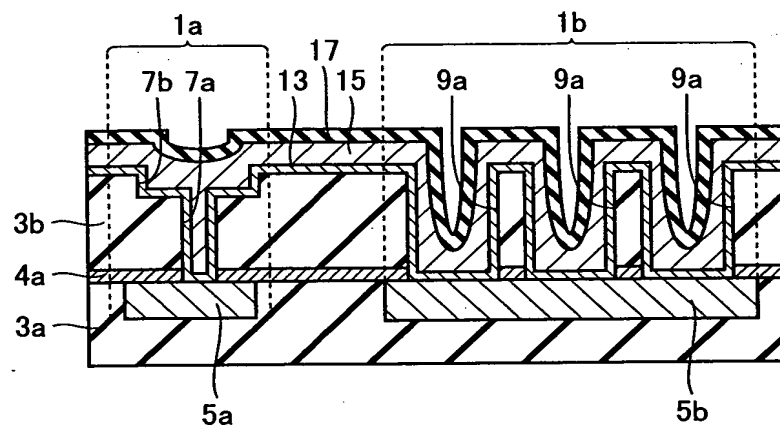


FIG.19

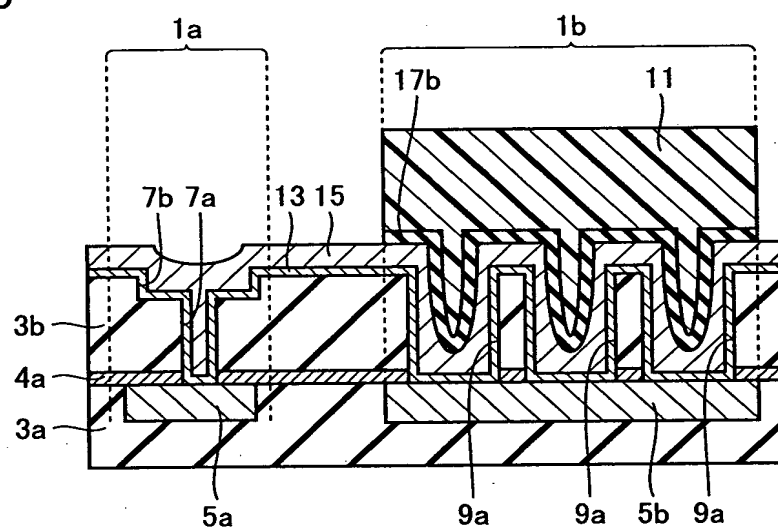


FIG.20

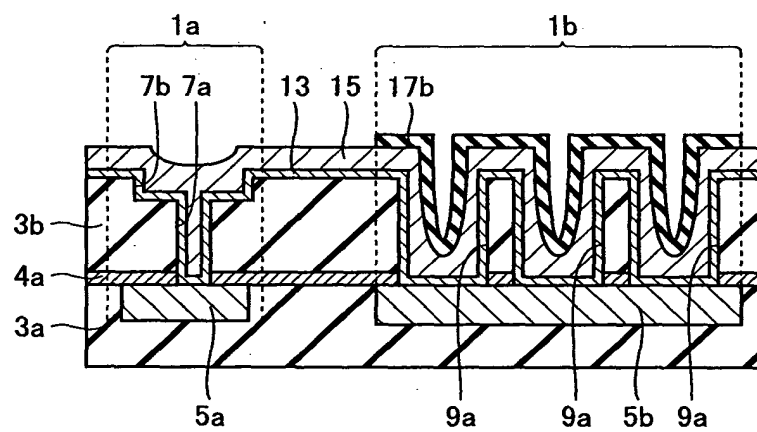


FIG.21

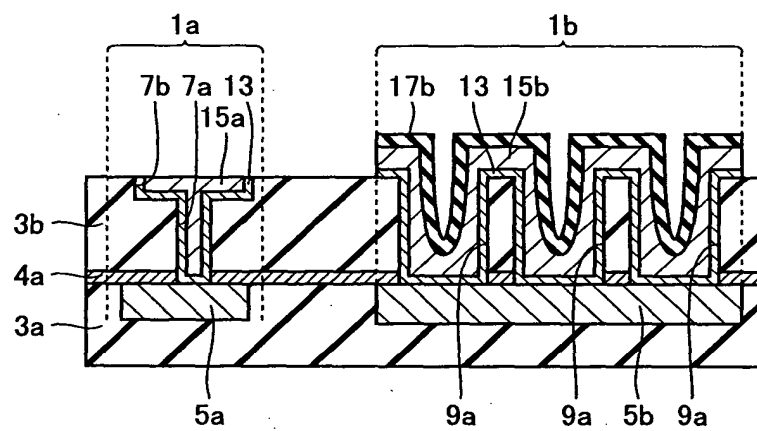


FIG.22

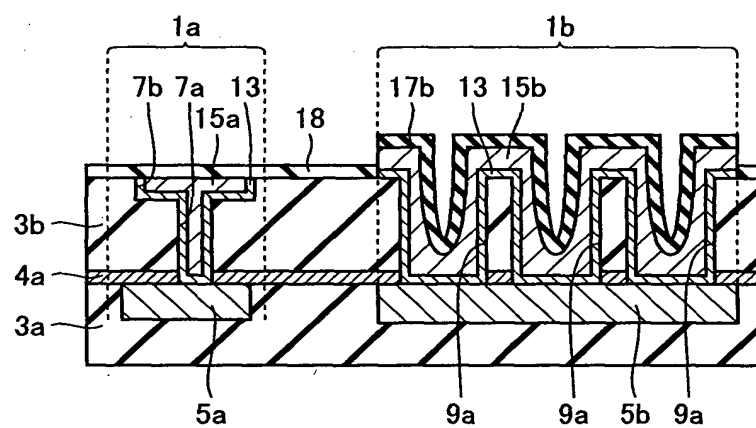


FIG.23

